

2015 International Symposium on Advanced Materials and Optoelectronics

Date

2015
Jan. 27
13:00~17:30

Venue

Saga
University
Japan

Synchrotron Light Application Center,
Saga University, Honjo 1, Saga, Japan
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Program

13:00-13:10

Opening Message

Qixin Guo Saga University

13:10-13:40

Terahertz spin spectroscopy by impulsive excitation of THz magnetic field

Makoto Nakajima Osaka University

13:40-14:10

Novel Approaches for Terahertz Generation, Detection, and Modulation

Zhenyu Zhao Shanghai Normal University

14:10-14:40

Photoinduced surface potential change of TiO₂ thin films observed by Kelvin force microscopy

Makoto Arita Kyushu University

14:40-15:10

Structural control of activated carbon using porous silica as a template

Ryoji Takahashi Ehime University

Break

15:30-16:00

Spectral reflectance monitoring of GaN epitaxial growth by MOCVD

Hyunseok Na Daejin University

16:00-16:30

Phase transformation and nanograin formation of semiconductor materials by high-pressure torsion
Yoshifumi Ikoma Kyushu University

16:30-17:00

Growth of ZnTe-based alloys for optoelectronic applications

Katsuhiko Saito Saga University

17:00-17:30

Epitaxy of AlGaN/GaN multiple quantum wells towards infrared detectors

Xinqiang Wang Peking University